



一 航 小 電 子 有 限 公 司
MOSDESIGN SEMICONDUCTOR CORP.

PIR CONTROLLER

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M7612

GENERAL DESCRIPTION 功能叙述

The M7612 is a PIR (passive infra-red) controller , using analog mixing digital design technique and manufactures by CMOS Process which can either drive TRIAC or RELAY depending on user's choice. With special noise immunity technique , M7612 is the most stable PIR controller you can find on the market. More than this , there are few components needed in its application circuit which can reduce material cost and increase competitive.

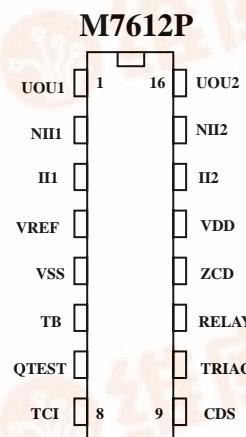
FEATURES 产品特长

- High noise immunity.
- Drive either RELAY or TRIAC.
- Adjustable light on duration.
- TRIAC can be either shunt or serial connected.
- PIR input.
- CDS input.
- Auto change on / auto mode by bonding option.
- 16 pin DIP or SOP package.

APPLICATIONS 产品应用

- PIR light controller, Motion Detector, Alarm system, Auto-door bell.

PIN ASSIGNMENT





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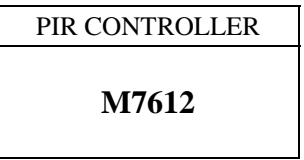
PIN DESCRIPTION

Pin No	Pin Name	Description
1	UOU1	First stage OP amp output.
2	NII1	First stage OP amp positive input.
3	II1	First stage OP amp negative input.
4	VREF	Stable reference voltage.
5	VSS	System ground.
6	TB	<p>Time base for: The delay time of receiving PIR signal to sent a pulse to trigger TRIAC or a high signal to trigger relay. The delay time = $R * C * 32$.</p> <p>The PIR signal patented and accepted only if the signal cycle greater than $R * C * 768$. When state of RELAY or TRIAC is changing form active into inactive mode. It takes more than $R * C * 4069$, then system is able to receive PIR signal again.</p> <p>$10K < R < 1M \text{ Ohm}$</p> <p>$100pF \leq C < 0.1\mu F$ (Reference Diagram 1)</p>
7	QTEST	For testing only.
8	TCI	<p>To set up the timing of how long TRIAC or RELAY is active. During the period , if the system receives the PIR signal , then it restarts counting the timing again. The flash cycle show the beginning of auto mode.</p> <p>Note: width of TRIAC pulse = $R * C * 2$</p> <p>Flash cycle: $R * C * 32768$</p> <p>The range for R: $4.7K \leq R < 1M \text{ Ohm}$</p> <p>C: $100pF < C < 0.1\mu F$ (Reference Diagram 2)</p>
9	CDS	<p>Connected to a CDS for inhibiting RELAY or TRIAC being triggered.</p> <p>If TRIAC or RELAY has already being triggered by PIR signal and turned into active mode , then CDS can not inhibit PIR again.</p>
10	TRAIC	<p>To trigger TRIAC , active low.</p> <p>Sink current: 15 mA max.</p>
11	RELAY	<p>To drive relay , active high.</p> <p>Sink current: 10 mA max.</p> <p>Source current: 10 mA max.</p>
12	ZCD	Detect zero cross of AC line under remote mode function.
13	VDD	Operation voltage: 5V , stand by current: 0.5 mA
14	II2	2 nd stage OP amp negative input.
15	NII2	2 nd stage OP amp positive input.
16	UOU2	2 nd stage OP amp output.





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DIAGRAM 1:

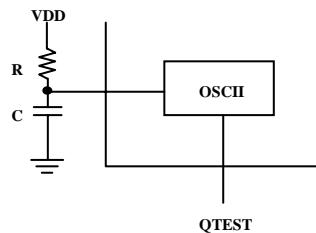
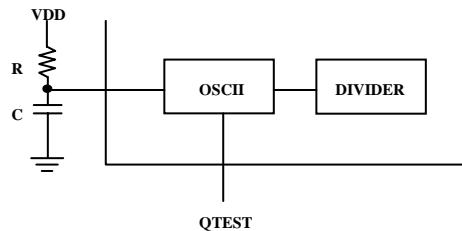
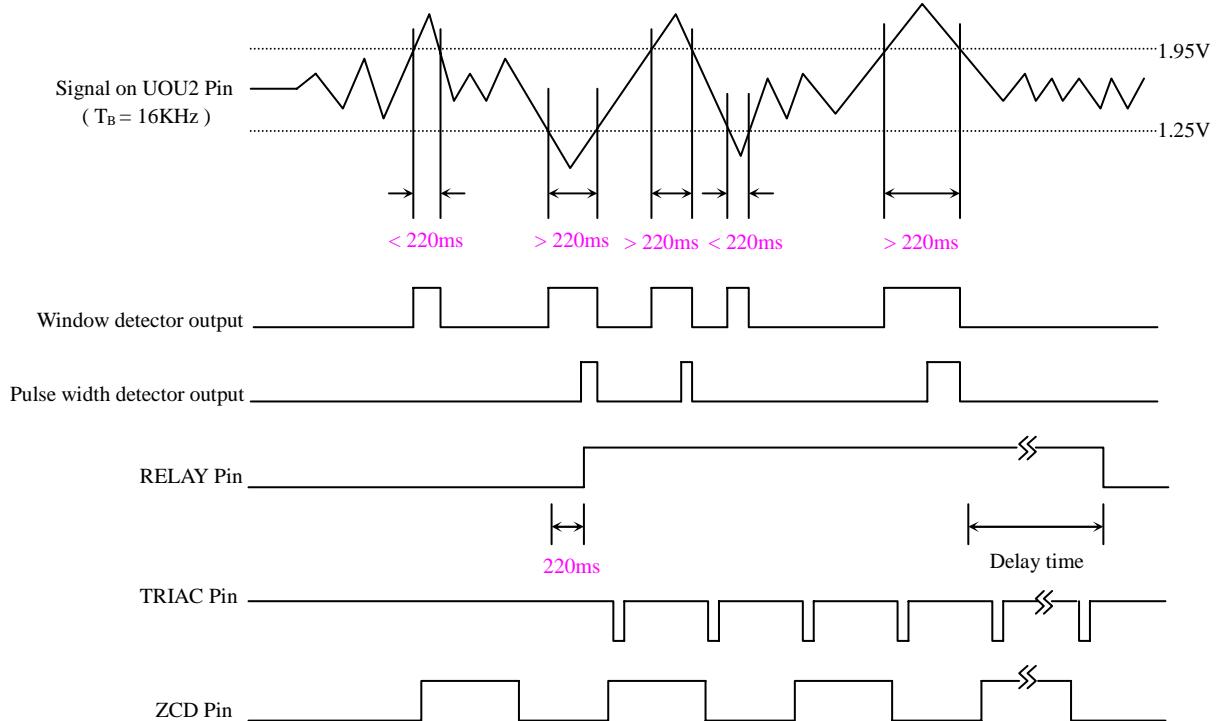


DIAGRAM 2:



TIMING RELATIONSHIP:





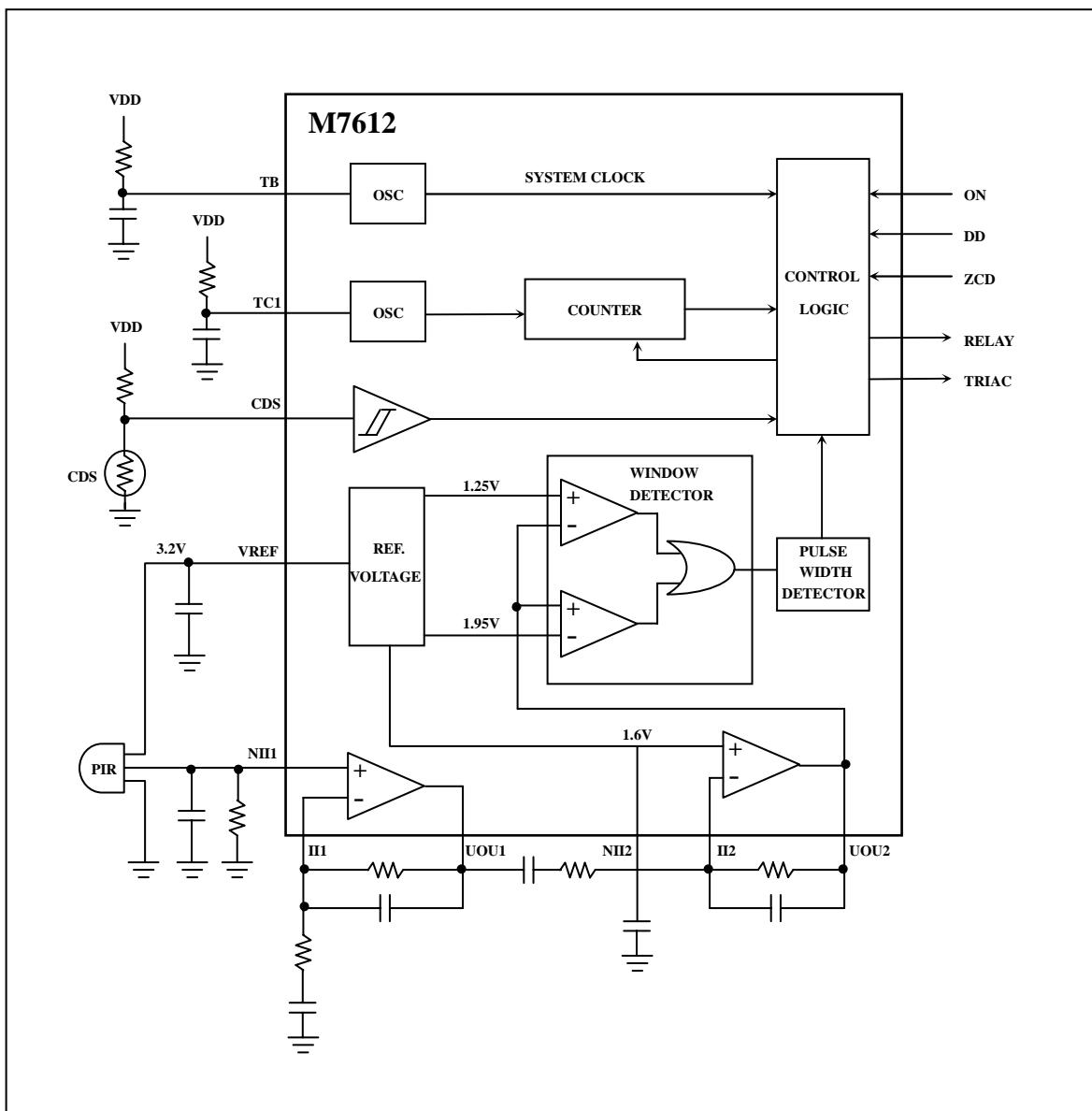
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BLOCK DIAGRAM





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ABSOLUTE MAXIMUM RATING

(TA=25°C)

Parameter	Sym.	Rating	Unit
Power Supply V _{DD} With Respect to V _{SS}	V _{DD} - V _{SS}	5.6	V
Voltage On Any Pin		-0.3 to 5.6	V
Operating Temperature	Top	-20 to 70	°C
Storage Temperature		-65 to 150	°C

ELECTRICAL CHARACTERISTICS

Characteristics	Sym.	Min.	Typ.	Max.	Unit	Conditions
Supply Voltage	V _{DD}	4.2	5	5.5	V	
Stand by Current	I _{ST}	0.9	1.0	1.2	mA	
Operating Current	I _{DD}	1.8	—	2.5	mA	1.8mA ,TRIAC / 2.5mA , RELAY
Stable Voltage	V _{REF}	3.0	3.2	3.4	V	V _{DD} > 4.2V
Source Current of V _{REF}	I _{REF}	200	—	—	uA	
Ripple of V _{REF}		—	—	0.5	mV	
Input and Output Regulation of V _{REF}		—	—	0.3%		
Time Base Operating Frequency	F _{TB}	15	16	17	KHz	
CDS Operating Trigger	V _{T+}	1.3	1.7	2.1	V	
CDS Operating Trigger	V _{T-}	0.6	0.9	1.1	V	
CDS Source Current	I _{CDS}	2.6	3.5	4.4	uA	
CDS Output Source Current	I _{SOURCE}	9	10.4	17.4	mA	
CDS Output Sink Current	I _{SINK}	11.6	13	21	mA	
Timer Duration of Out 1	T _{OUT1}	10	—	1300	SEC	C=0.01uF , R=4.7K-1M
		0.1	—	13		C=100pF , R=4.7K-1M
Relay Source Current	I _{RS}	—	—	10	mA	
Relay Sink Current	I _{RSINK}	—	—	10	mA	
Relay Operating Voltage	V _{RO}	13.1	—	18.8	V	
TRIAC Sink Current	I _{TSINK}	—	—	15	mA	
TRIAC Source Current	I _{TSOURCE}	—	—	50	uA	





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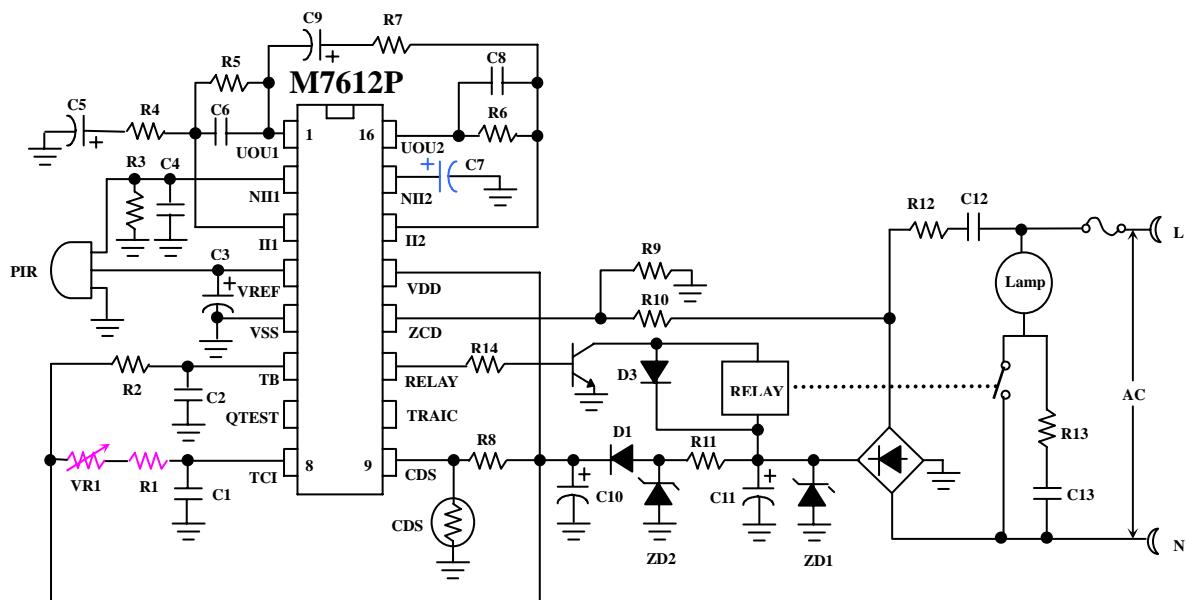
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ELECTRICAL CHARACTERISTICS 电气规格

一. RELAY APPLICATION



C1	0.01uF
C2	100pF
C3	100uF
C4	0.01uF
C5	33uF
C6	0.1uF
C7	47uF
C8	0.047uF
C9	47uF
C10	100uF/10V
C11	220uF/25V
C12	0.47uF/400~600V
C13	0.047uF/400~600V

VR1	1MΩ
R1	4.7KΩ
R2	620KΩ
R3	47KΩ
R4	15KΩ
R5	820KΩ
R6	560KΩ
R7	15KΩ
R8	51KΩ
R9	470KΩ
R10	1MΩ
R11	2.4KΩ
R12	47Ω/ 1/2W

R13	100Ω/ 1/2W
R14	5.6KΩ
D1	1N4001
D3	1N4148
ZD1	12V
ZD2	5.6V

M7612 TCI PIN 外加电阻、电容与 Delay 时间的关系

电容	电阻	频率	DELAY 时间(秒)
103	4.7K	40KHz	10
103	10K	20KHz	16
103	20K	10KHz	28
103	100K	2KHz	130
103	200K	0.8KHz	260
103	1M	0.2KHz	1300

Note:

- (1) To adjust delay time , change VR1 value. (VR1=1M , delay time is \geq 10 sec)
- (2) For different CDS , R8 value should be adjusted.





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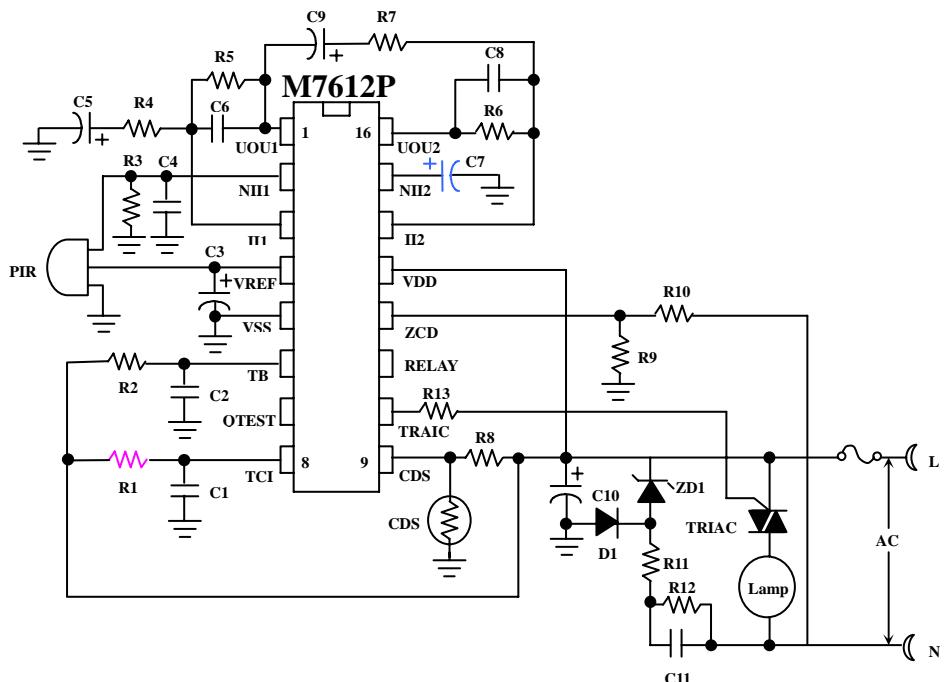
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二. TRIAC APPLICATION

(A) 应用一



C1	0.01uF
C2	100pF
C3	100uF
C4	0.01uF
C5	33uF
C6	0.1uF
C7	47uF
C8	0.047uF
C9	47uF
C10	100uF/10V
C11	0.1uF/400~600V
D1	1N4004
ZD1	5.6V

R1	見附表
R2	620KΩ
R3	47KΩ
R4	15KΩ
R5	820KΩ
R6	560KΩ
R7	15KΩ
R8	51KΩ
R9	470KΩ
R10	1MΩ
R11	47Ω / 1/2W
R12	100KΩ
R13	330Ω

M7612 TCI PIN 外加电阻、电容与 Delay 时间的关系

电容	R1 电阻	频率	DELAY 时间(秒)
103	4.7K	40KHz	10
103	10K	20KHz	16
103	20K	10KHz	28
103	100K	2KHz	130
103	200K	0.8KHz	260
103	1M	0.2KHz	1300

Note:

- (1) To adjust delay time , change R1 value. (Delay time is ≥ 10 sec)
- (2) For different CDS , R8 value should be adjusted.





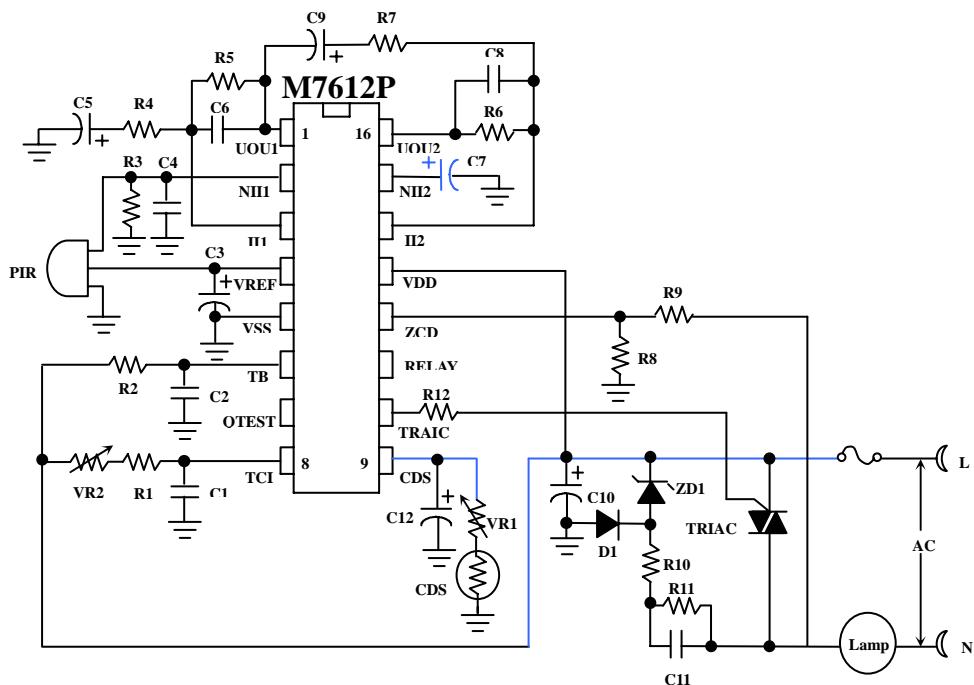
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(B) 应用二



C1	0.01uF
C2	100pF
C3	100uF / 16V
C4	0.01uF
C5	220uF / 10V
C6	0.1uF
C7	22uF / 16V
C8	683 pF
C9	47uF / 16V
C10	470uF / 16V
C11	0.15uF / 400~600V
C12	1uF / 50V
D1	1N4007
ZD1	6.2V

VR1	1MΩ
VR2	1MΩ
R1	4.7KΩ
R2	620KΩ
R3	47KΩ
R4	47KΩ
R5	220KΩ
R6	470KΩ
R7	56KΩ
R8	800KΩ
R9	720KΩ
R10	47Ω / 1/2W
R11	100KΩ
R12	100Ω

M7612 TCI PIN 外加电阻、电容与 Delay 时间的关系

电容	电阻	频率	DELAY 时间(秒)
103	4.7K	40KHz	10
103	10K	20KHz	16
103	20K	10KHz	28
103	100K	2KHz	130
103	200K	0.8KHz	260
103	1M	0.2KHz	1300

Note:

- (1) To adjust delay time , change VR2 value. (VR2=1M , delay time is ≥ 10 sec)
- (2) For different CDS , VR1 value should be adjusted.
- (3) Distance = 4m.





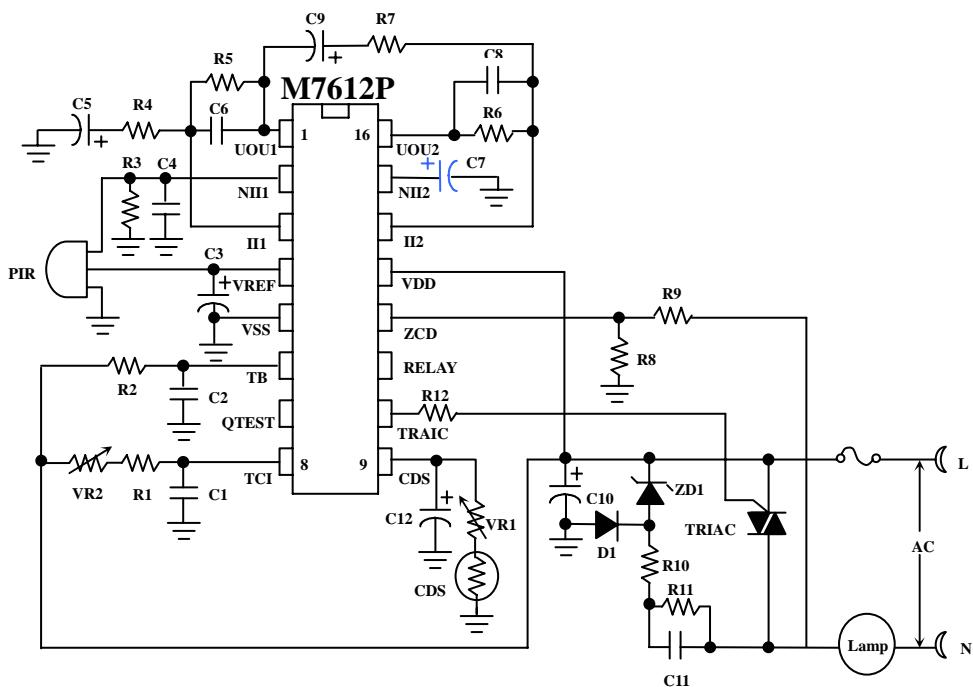
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(C) 应用三



C1	0.01uF
C2	100pF
C3	100uF / 16V
C4	0.01uF
C5	33uF / 16V
C6	0.033uF
C7	22uF / 16V
C8	0.033 uF
C9	33uF / 16V
C10	470uF / 16V
C11	0.33uF / 400~600V
C12	1uF / 50V
D1	1N4007
ZD1	6.2V

VR1	1MΩ
VR2	1MΩ
R1	4.7KΩ
R2	620KΩ
R3	47KΩ
R4	15KΩ
R5	820KΩ
R6	820KΩ
R7	15KΩ
R8	800KΩ
R9	720KΩ
R10	47Ω / 1/2W
R11	100KΩ
R12	100Ω

M7612 TCI PIN 外加电阻、电容与 Delay 时间的关系

电容	电阻	频率	DELAY 时间(秒)
103	4.7K	40KHz	10
103	10K	20KHz	16
103	20K	10KHz	28
103	100K	2KHz	130
103	200K	0.8KHz	260
103	1M	0.2KHz	1300

Note:

- (1) To adjust delay time , change VR2 value. (VR2=1M , delay time is ≥ 10 sec)
- (2) For different CDS , VR1 value should be adjusted.
- (3) Distance = 8m.

* All specs and applications shown above subject to change without prior notice.
(以上电路及规格仅供参考,本公司得径行修正)

